

# L1SS400GT1G

## S-L1SS400GT1G

### Switching Diode

#### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Extremely small surface mounting type.
- High Speed.
- High reliability.

#### 2. Applications

- High speed switching

#### 3. DEVICE MARKING AND RESISTOR VALUES

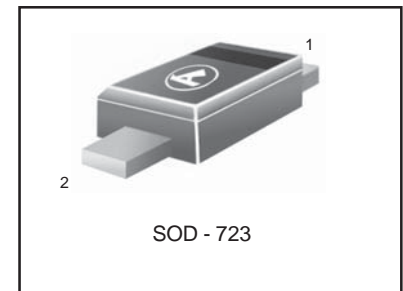
Device	Marking	Shipping
L1SS400GT1G	3	4000/Tape&Reel
L1SS400GT5G	3	8000/Tape&Reel

#### 4. MAXIMUM RATINGS(Ta = 25°C)

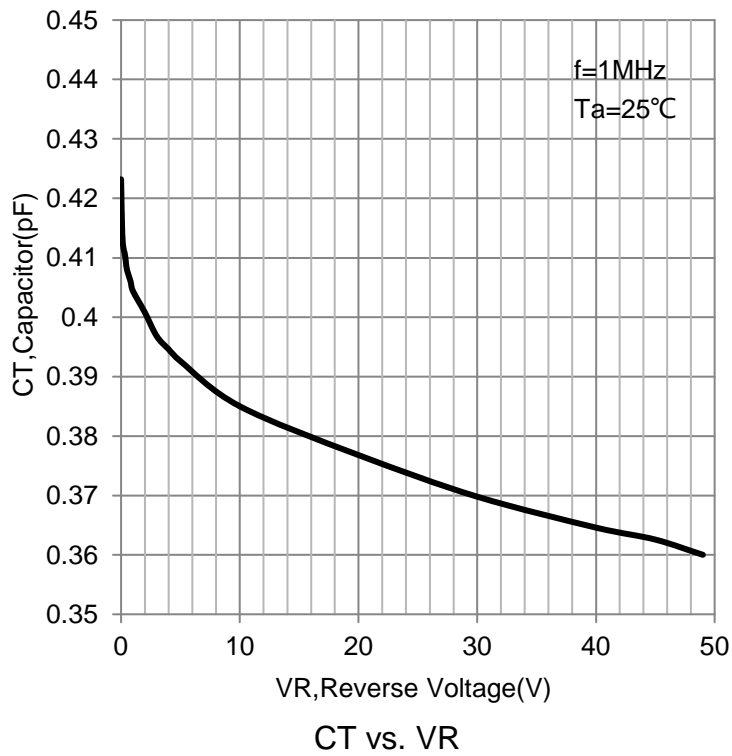
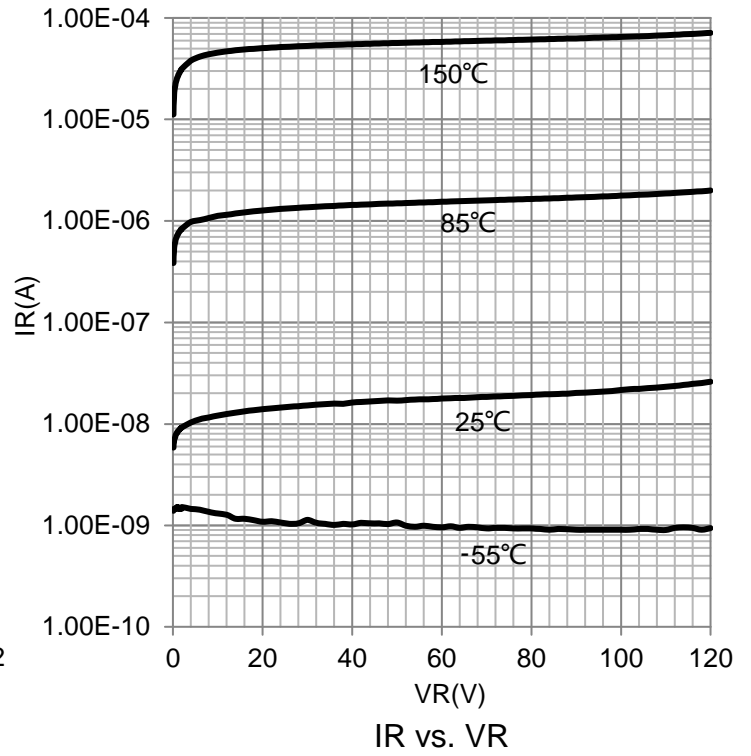
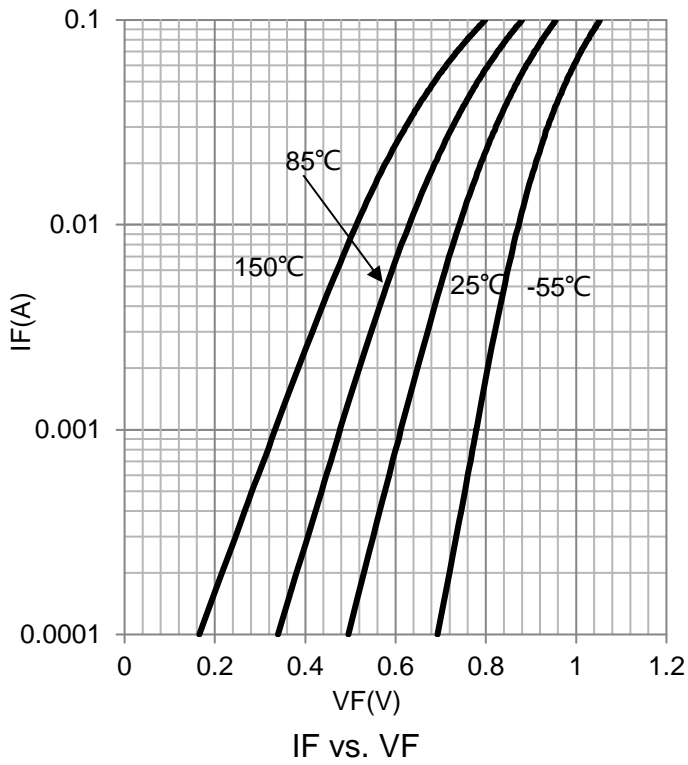
Parameter	Symbol	Limits	Unit
Peak reverse voltage	VRM	90	V
DC reverse voltage	VR	80	V
Peak forward current	IFM	225	mA
Mean rectifying current	IO	100	mA
Surge current (1s)	Isurge	500	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55~+125	°C

#### 5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

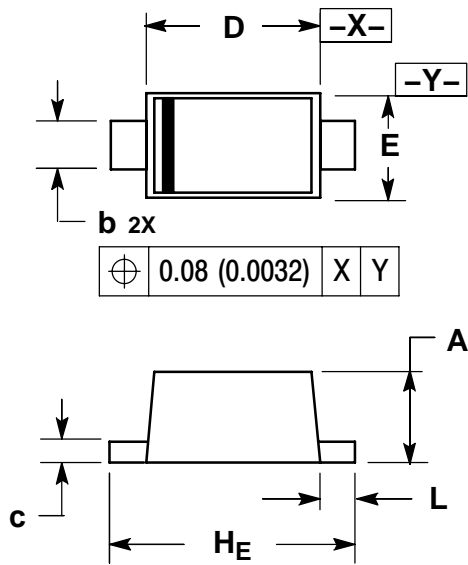
CHARACTERISTICS	Symbol	Min	Typ	Max	Unit
Forward voltage (IF=100mA)	VF	-	-	1.2	V
Reverse current (VR=80V)	IR	-	-	0.1	μA
Capacitance between terminals (VR=0.5V,f=1MHz)	CT	-	0.72	3	pF
Reverse recovery time (VR=6V,IF=10mA,RL=100Ω)	Trr	-	-	4	ns



### 6.ELECTRICAL CHARACTERISTICS CURVES



### 7.OUTLINE AND DIMENSIONS



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

Dim	MILLIMETERS			NCES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.2	0.25	0.006	0.0079	0.010

### 8.SOLDERING FOOTPRINT

